

40V N-Channel Enhancement Mode MOSFET

Voltage 40 V Current 43 A

Features

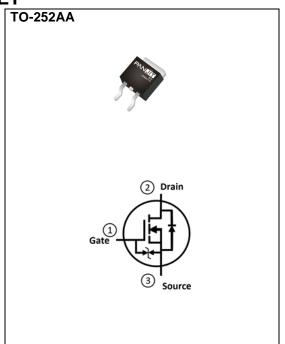
- RDS(ON), VGS@10V, ID@20A<10.6m Ω
- RDS(ON), VGS@4.5V, ID@10A<14.6m Ω
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.3217 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current(Note 3)	T _C =25°C		43		
	Tc=100°C	l _D	31	Α	
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	172		
Power Dissipation	T _C =25°C	D	36	10/	
	T _C =100°C	Po	18	W	
Continuous Drain Current(Note 4)	T _A =25°C		12.5		
	T _A =70°C	ID	10.5	A	
Power Dissipation	T _A =25°C	D.	3	14/	
	T _A =70°C	Po	2.1	W	
Single Pulse Avalanche Energy(Note 5)		Eas	20	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Thermal Resistance ^(Note 4)	Junction to Case	R _{θJC}	4.2	°C/W	
	Junction to Ambient	$R_{\theta JA}$	50		



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	40			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =50uA	1.1	1.6	2.3	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	8.3	10.6	mΩ
		V _{GS} =4.5V, I _D =10A	-	11.2	14.6	11152
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	±1	uA
0-4- 0	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±10	uA
Gate-Source Leakage Current		V _{GS} =±10V, VDS=0V	-	-	±1	
Dynamic ^(Note 6)						
Total Gate Charge	Qg		-	13	-	nC
Gate-Source Charge	Q_{gs}	V _{DS} =32V, I _D =20A,	-	3	-	
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	2	-	
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V,	-	744	-	pF
Output Capacitance	Coss		-	159	-	
Reverse Transfer Capacitance	Crss	f=1MHz	-	29	-	
Gate resistance	Rg	f=1MHz	-	1.6	-	Ω
Turn-On Delay Time	td _(on)	\/ 00\/ L 00A	-	9	-	
Turn-On Rise Time	t _r	V _{DS} =32V, I _D =20A,	-	3	-	ns
Turn-Off Delay Time	td _(off)	$V_{GS}=10V, R_{G}=3\Omega$	-	21	-	
Turn-Off Fall Time	tf	(1.010 2)	-	3	-	
Drain-Source Diode						
Diode Forward Current	Is	Tc=25°C	-	-	43	A
Pulsed Diode Forward Current	I _{SM}	10=25 U	-	-	172	
Diode Forward Voltage	V _{SD}	Is=20A, V _G s=0V	-	0.9	1.3	V
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =20A	-	21	-	ns
Reverse Recovery Charge	Qrr	dls/dt=100A/us	-	10	-	nC

NOTES:

- 1. Pulse width<a>100us, Duty cycle<a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an R_{0JC}=4.2°C/W.
- 4. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH, I_{AS}=9A, V_{DD}=30V, V_{GS}=10V, Starting T_J=25°C. the chip is about to carry I_{AS}≈18A.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

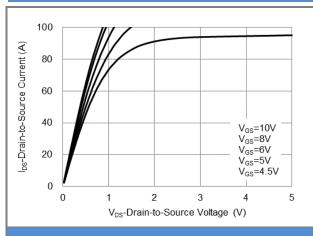


Fig.1 On-Region Characteristics

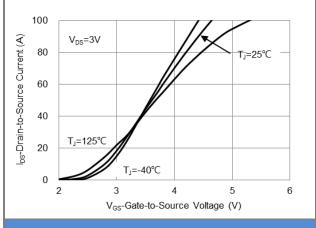


Fig.2 Transfer Characteristics

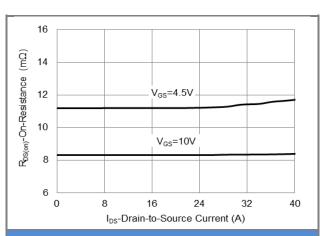


Fig.3 On-Resistance vs. Drain Current

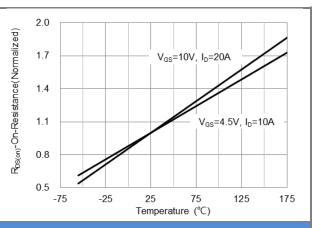
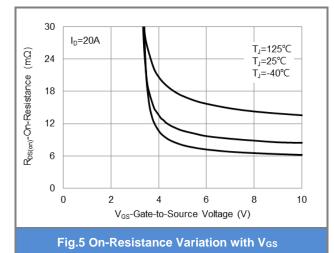


Fig.4 On-Resistance vs. Junction temperature



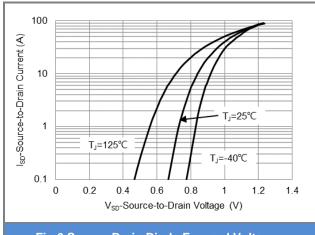


Fig.6 Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTIC CURVES

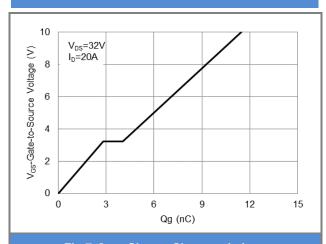


Fig.7 Gate-Charge Characteristics

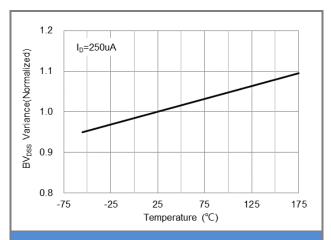


Fig.8 Breakdown Voltage Variation vs. Temperature

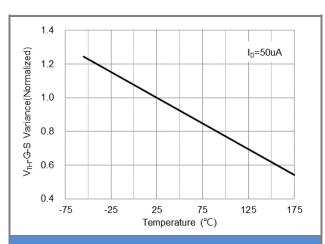


Fig.9 Threshold Voltage Variation with Temperature

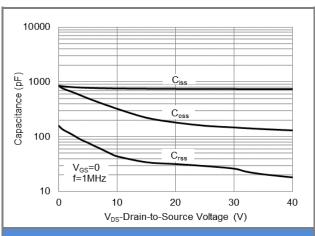
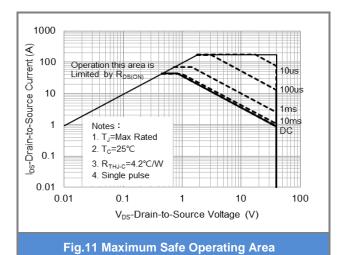


Fig.10 Capacitance vs. Drain-Source Voltage



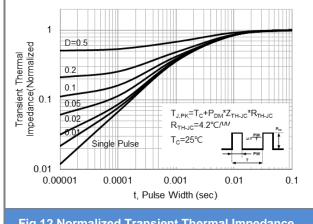


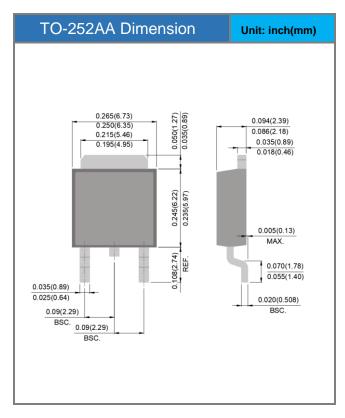
Fig.12 Normalized Transient Thermal Impedance

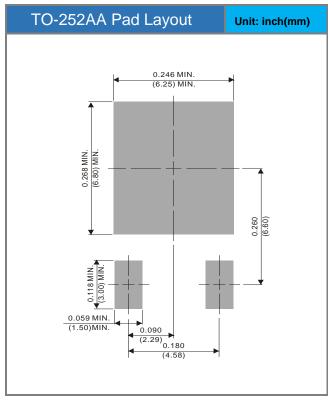


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJD30N04S-AU	TO-252AA	3K pcs / 13" reel	D30N04S	

Packaging Information & Mounting Pad Layout







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